Microsemi
POWER PRODUCTS GROUP

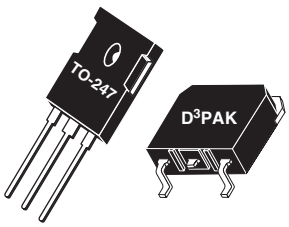
APT53N60BC6
APT53N60SC6

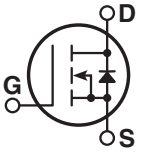
600V 53A 0.070Ω

COOLMOS
Power Semiconductors

Super Junction MOSFET

- Ultra Low $R_{DS(ON)}$
- Low Miller Capacitance
- Ultra Low Gate Charge, Q_g
- Avalanche Energy Rated
- Extreme dv/dt Rated
- Popular TO-247 or Surface Mount D^3 package.





MAXIMUM RATINGS

All Ratings per die: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT53N60B_SC6	UNIT
V_{DSS}	Drain-Source Voltage	600	Volts
I_D	Continuous Drain Current @ T_C = 25°C	53	Amps
	Continuous Drain Current @ T_C = 100°C	34	
I_{DM}	Pulsed Drain Current [1]	159	
V_{GS}	Gate-Source Voltage Continuous	±20	Volts
P_D	Total Power Dissipation @ T_C = 25°C	417	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	- 55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	260	
I_{AR}	Avalanche Current [2]	9.3	Amps
E_{AR}	Repetitive Avalanche Energy [2] (Id =9.3A, Vdd = 50V)	1.72	mJ
E_{AS}	Single Pulse Avalanche Energy (Id = 9.3A, Vdd = 50V)	1135	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{(DSS)}$	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250µA)	600			Volts
$R_{DS(on)}$	Drain-Source On-State Resistance [3] (V_{GS} = 10V, I_D = 25.8A)			0.070	Ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = 600V, V_{GS} = 0V)			25	µA
	Zero Gate Voltage Drain Current (V_{DS} = 600V, V_{GS} = 0V, T_C = 150°C)			250	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±20V, V_{DS} = 0V)			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.72mA)	2.5	3	3.5	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trade-mark of Infineon Technologies AG."

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		4020		pF
C_{oss}	Output Capacitance			3545		
C_{rss}	Reverse Transfer Capacitance			330		
Q_g	Total Gate Charge [4]	V_{GS} = 10V V_{DD} = 300V I_D = 53A @ 25°C		154		nC
Q_{gs}	Gate-Source Charge			26		
Q_{gd}	Gate-Drain ("Miller") Charge			82		
$t_{d(on)}$	Turn-on Delay Time	**INDUCTIVE SWITCHING** V_{GS} = 15V V_{DD} = 400V I_D = 53A @ 125°C R_G = 4.3Ω		14		ns
t_r	Rise Time			36		
$t_{d(off)}$	Turn-off Delay Time			151		
t_f	Fall Time			74		
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 25℃** V_{DD} = 400V, V_{GS} = 15V I_D = 53A, R_G = 4.3Ω		960		µJ
E_{off}	Turn-off Switching Energy			873		
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 125℃** V_{DD} = 400V, V_{GS} = 15V I_D = 53A, R_G = 4.3Ω		1478		
E_{off}	Turn-off Switching Energy			995		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)				46	Amps
I_{SM}	Pulsed Source Current [1] (Body Diode)				159	
V_{SD}	Diode Forward Voltage [3] (V_{GS} = 0V, I_S = -53A)			0.9	1.2	Volts
$^{dv}/_{dt}$	Peak Diode Recovery $^{dv}/_{dt}$ [6]				15	V/ns
t_{rr}	Reverse Recovery Time (I_S = -53A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		795		ns
Q_{rr}	Reverse Recovery Charge (I_S = -53A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		25		µC
I_{RRM}	Peak Recovery Current (I_S = -53A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		58		Amps

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.30	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

1 Repetitive Rating: Pulse width limited by maximum junction temperature

2 Repetitive avalanche causes additional power losses that can be calculated as ***$P_{AV} = E_{AR}*f$. Pulse width tp limited by Tj max.***

3 Pulse Test: Pulse width < 380 µs, Duty Cycle < 2%

4 See MIL-STD-750 Method 3471

5 Eon includes diode reverse recovery.

6 Maximum 125°C diode commutation speed = di/dt 600A/µs

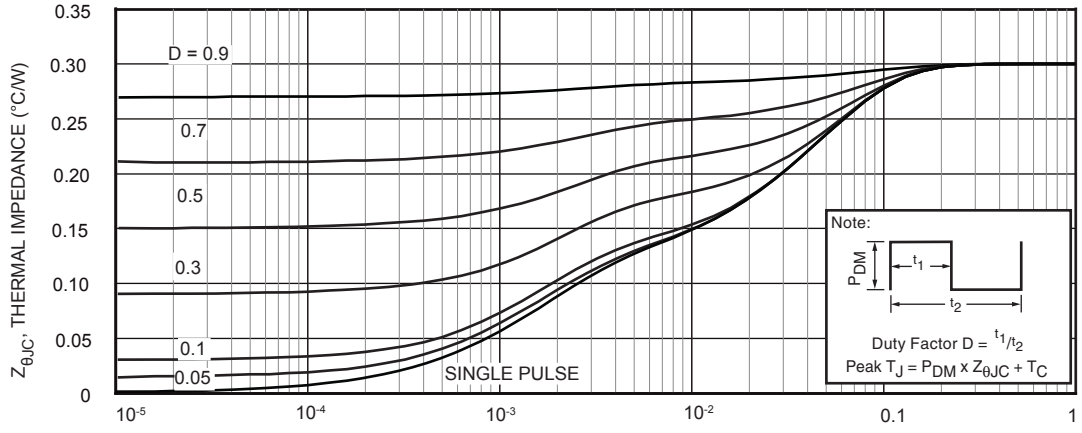


Figure 1, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

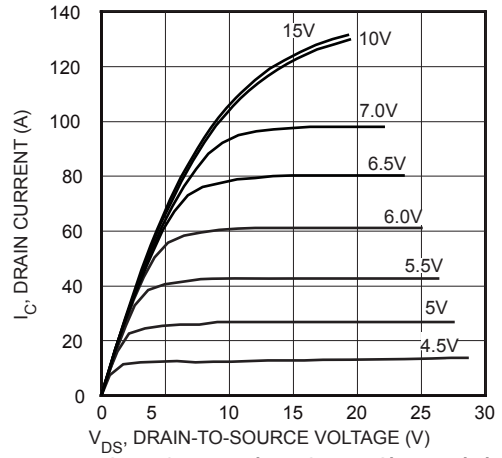


FIGURE 2, Low Voltage Output Characteristics

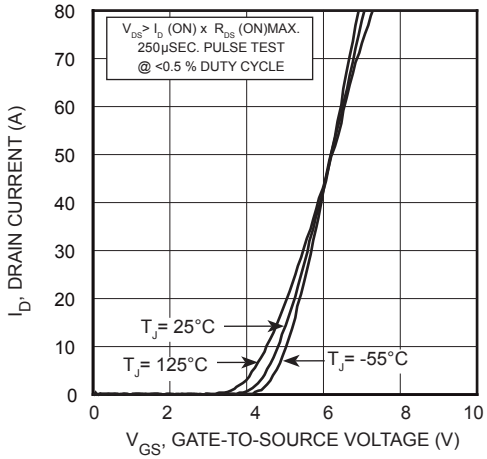


FIGURE 3, Transfer Characteristics

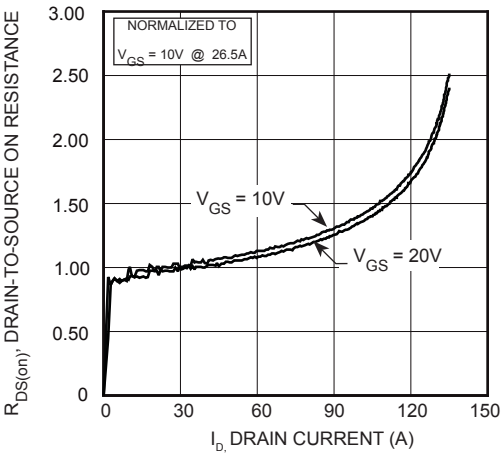


FIGURE 4, R_{DS}(ON) vs Drain Current

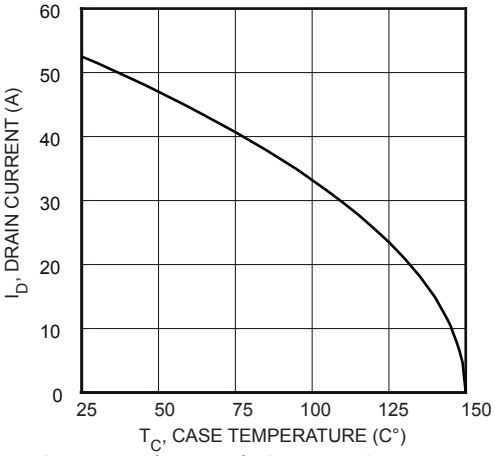


FIGURE 5, Maximum Drain Current vs Case Temperature

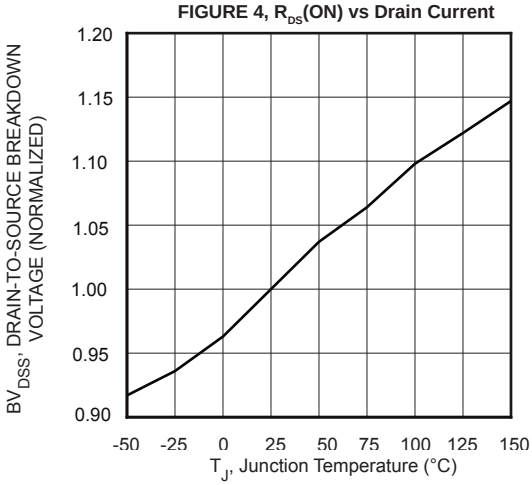


FIGURE 6, Breakdown Voltage vs Temperature

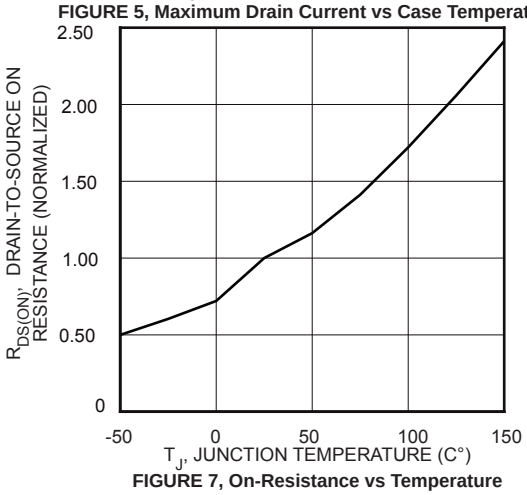


FIGURE 7, On-Resistance vs Temperature

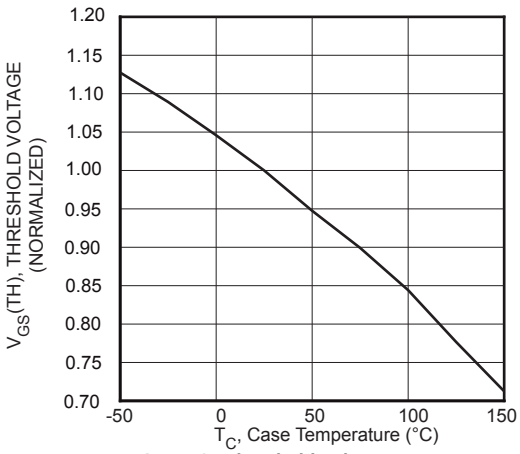


FIGURE 8, Threshold Voltage vs Temperature

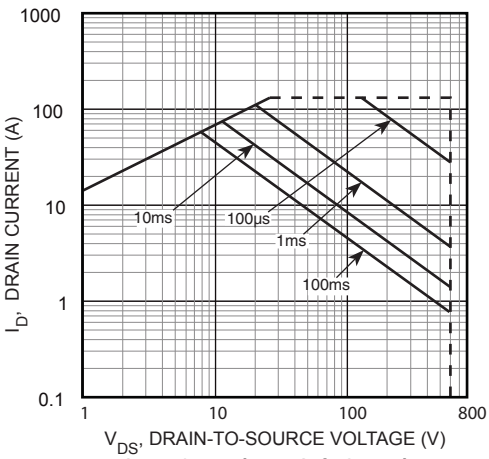


FIGURE 9, Maximum Safe Operating Area

Typical Performance Curves

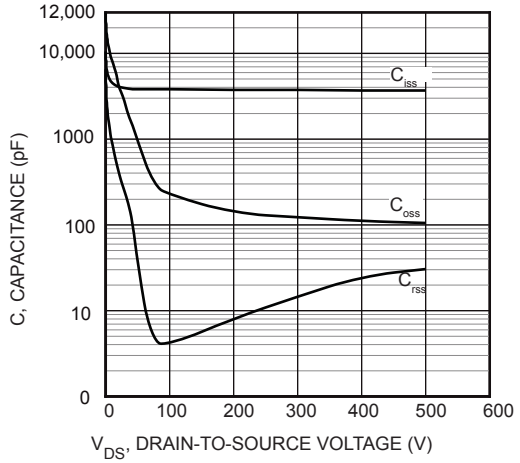


FIGURE 10, Capacitance vs Drain-To-Source Voltage

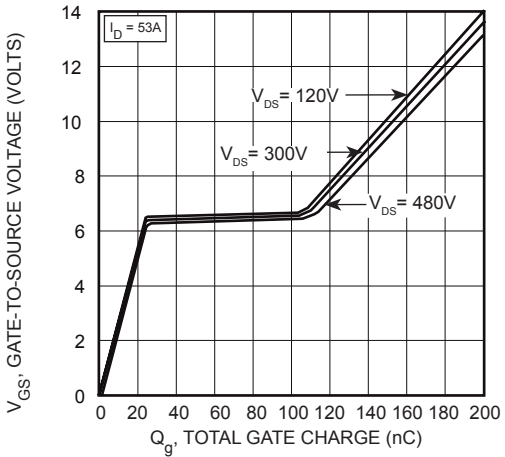


FIGURE 11, Gate Charges vs Gate-To-Source Voltage

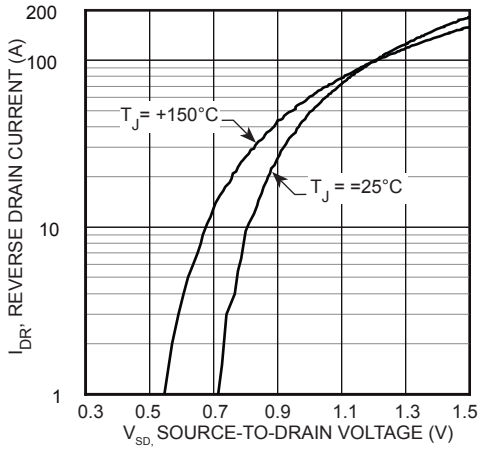


FIGURE 12, Source-Drain Diode Forward Voltage

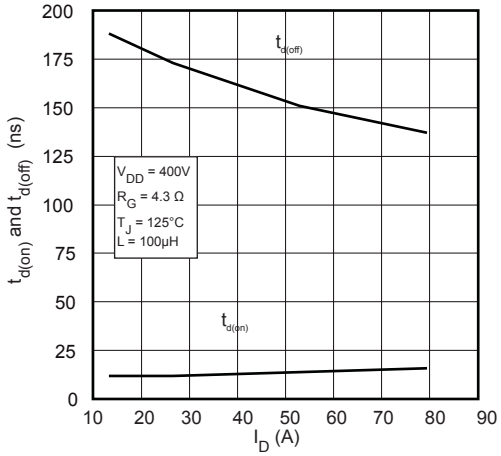


FIGURE 13, Delay Times vs Current

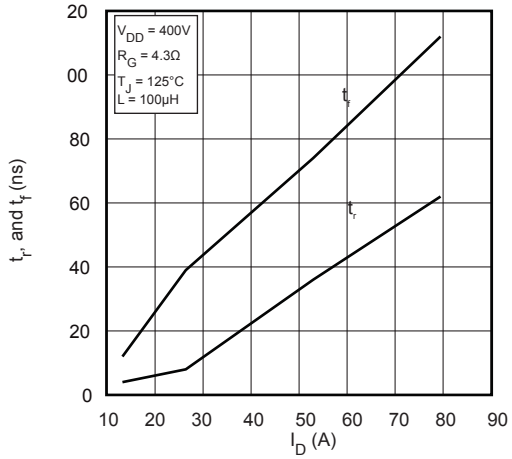


FIGURE 14 , Rise and Fall Times vs Current

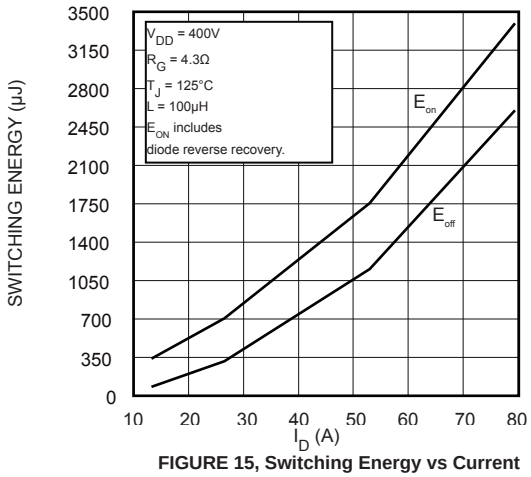


FIGURE 15, Switching Energy vs Current

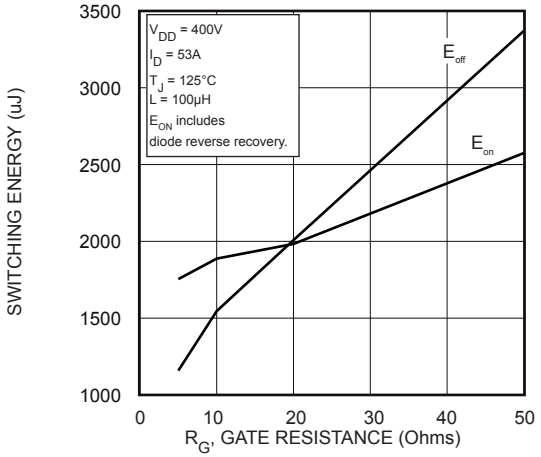


FIGURE 16, Switching Energy vs Gate Resistance

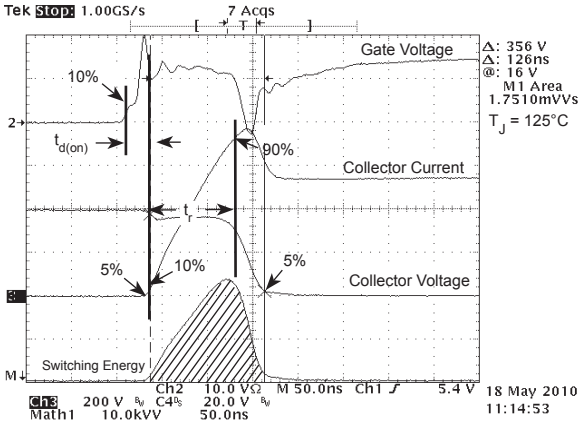


Figure 17, Turn-on Switching Waveforms and Definitions

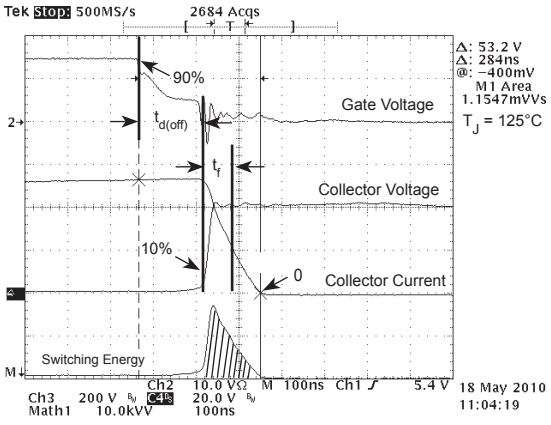


Figure 18, Turn-off Switching Waveforms and Definitions

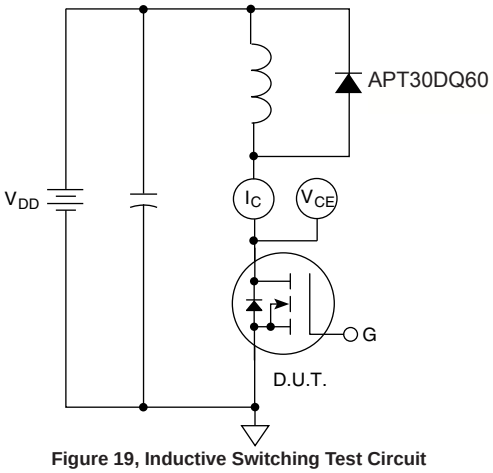
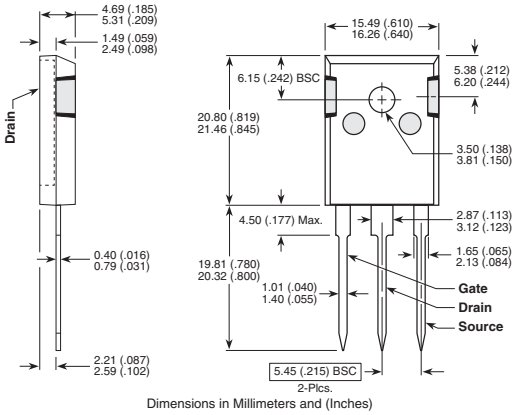


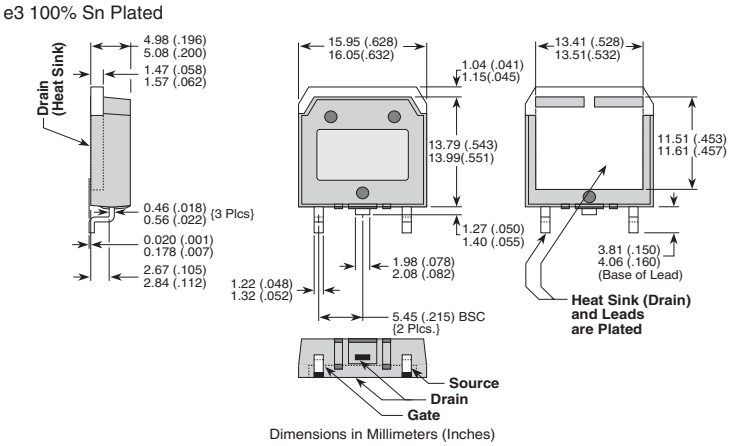
Figure 19, Inductive Switching Test Circuit

TO-247 (B) Package Outline



Dimensions in Millimeters and (Inches)

D^{3}PAK Package Outline



Dimensions in Millimeters (Inches)